	τ_Y (60°C)	τ_Y (20°C)
Standard silicon	90 min	1.3 y
SINTEF	220 min	3.2 y
CiS	350 min	5 y
STMicroelectronics	450 min	6.5 y

Table 1.: Reverse annealing time constants τ_Y as measured at 60°C for standard and oxygenated silicon produced by three different manufacturers. The activation energy given in Ref. [6] has been used to scale the time constant to 20°C.

	Standard Silicon		Oxygen-enriched Silicon	
	Neutrons	Protons	Neutrons	Protons
g_a	1.8×10^{-2} cm^{-1}	-	1.4×10^{-2} cm^{-1}	-
τ_a(20°C)	55 h	-	70 h	-
g_C	1.5×10^{-2} cm^{-1}	1.9×10^{-2} cm^{-1}	2.0×10^{-2} cm^{-1}	5.3×10^{-3} cm^{-1}
N_{C0}/N_{eff0}	0.70	-	0.45	1.0
g_Y	5.2×10^{-2} cm^{-1}	6.6×10^{-2} cm^{-1}	4.8×10^{-2} cm^{-1}	2.3×10^{-2} cm^{-1} (♣)
τ_Y(20°C)	480 d	-	800 d	950 d

(♣) saturation value measured for $\Phi_{eq} = 6\ 10^{14}$cm^{-2}

Table 2.: Damage parameters for standard and oxygen enriched silicon as given in Ref.[3] and used for the damage projections shown in Fig. 13. The new data given in Table 1 have not been considered yet.